L Number	Hits	Search Text	DB	Time stamp
1	2930000	memory or storage	USPAT;	2004/10/17 15:59
			US-PGPUB;	' '
			EPO; JPO;	
			DERWENT	
2	28893	(memory or storage) and resistance with cell	USPAT;	2004/10/17 16:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
3	13957	(memory or storage) and resistive with (cell or element or	USPAT;	2004/10/17 16:02
_		unit)	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
4	41173	((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))	USPAT;	2004/10/17 16:02
			US-PGPUB;	2001/10/17 10:02
		220.4gg/ and 100.0010 Mar (00.00 of clotheric of anic)	EPO; JPO;	
			DERWENT	
5	3181	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:10
	3101	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	200 1/10/17 10:10
		select\$5 adj2 (transistor or element)	EPO; JPO;	
		Solocity days (dailolotty)	DERWENT	
6	833	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:03
	055	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2004/10/17 10.03
		select\$5 adj2 (transistor or element)) and (mram or	EPO; JPO;	
		magnetic)	DERWENT	
7	1301	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:04
1	1501	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2007/10/17 10:04
	•	select\$5 with diode	EPO; JPO;	
			DERWENT	
8	373	(((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:09
٦	3/3	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2007/10/17 10:03
		select\$5 adj2 (transistor or element)) and (mram or	EPO; JPO;	
		magnetic)) and 365/\$.ccls.	DERWENT	
10	39	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:17
10	39	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2007/10/17 10:17
		variable adj resistive) and select\$5 adj2 (transistor or	EPO; JPO;	
		element)	DERWENT	
9	162	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:14
	102	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	200 1/10/17 10:14
		variable adj resistive	EPO; JPO;	
		Tanabio adji colodito	DERWENT	
11	3439	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:17
**	5,35	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	200 1/10/17 10:17
		resist\$6 with diode	EPO; JPO;	, ,
		1 cologo mui diodo	DERWENT	
12	1040	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:17
**	10-10	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	200 1/10/17 10:17
		resist\$6 with diode) and cell with diode	EPO; JPO;	
		1 1000 That aloue) and cell that aloue	DERWENT	
13	425	(((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:18
13	723	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	200 1/10/17 10:10
		resist\$6 with diode) and cell with diode) and 365/\$.ccls.	EPO; JPO;	
		Tests with aloue, and cell with aloue, and 303/\$.ccis.	DERWENT	
	L	<u> </u>	DEKAAEIAI	<u> </u>

L Number	Hits	Search Text	DB	Time stamp
1	2930000	memory or storage	USPAT;	2004/10/17 15:59
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
2	28893	(memory or storage) and resistance with cell	USPAT;	2004/10/17 16:01
			US-PGPUB;	
			EPO; JPO;	
			DERWENT	
3	13957	(memory or storage) and resistive with (cell or element or	USPAT;	2004/10/17 16:02
		unit)	US-PGPUB;	
			EPO; JPO;	
4	41173	((mamon, or storage) and resistance with cell \ ((memon, or	DERWENT	2004/10/17 16:02
"	411/3	((memory or storage) and resistance with cell) ((memory or storage) and resistive with (cell or element or unit))	USPAT; US-PGPUB;	2004/10/17 16:02
		storage) and resistive with (cen of element of time))	EPO; JPO;	
			DERWENT	
5	3181	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:10
	5252	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2001/10/17 10:10
		select\$5 adj2 (transistor or element)	EPO; JPO;	
		,	DERWENT	
6	833	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:03
		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	
		select\$5 adj2 (transistor or element)) and (mram or	EPO; JPO;	·
		magnetic)	DERWENT	
7	1301	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:04
		or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	,
		select\$5 with diode	EPO; JPO;	
	373	////maman, ou stauses) and vasistance with a II \//	DERWENT	2004/40/47 46 60
8	373	(((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:09
		or storage) and resistive with (cell or element or unit))) and select\$5 adj2 (transistor or element)) and (mram or	US-PGPUB; EPO; JPO;	, i
		magnetic)) and 365/\$.ccls.	DERWENT	
9	162	(((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:10
	102	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	2007/10/17 10.10
		variable adj resistive	EPO; JPO;	
		· ·	DERWENT	
10	39	((((memory or storage) and resistance with cell) ((memory	USPAT;	2004/10/17 16:12
	- 2	or storage) and resistive with (cell or element or unit))) and	US-PGPUB;	
		variable adj resistive) and select\$5 adj2 (transistor or	EPO; JPO;	
		element)	DERWENT	